

**FAIRCHILD**  
SEMICONDUCTOR®

July 2001

**IGBT**

## FMBL1G200US60

### Molding Type Module

#### General Description

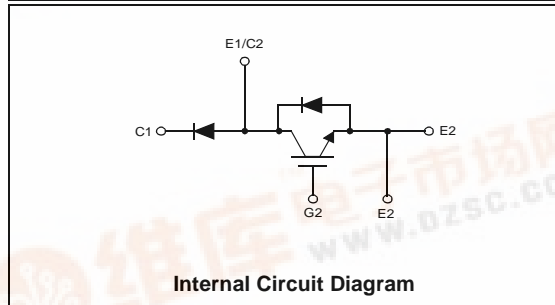
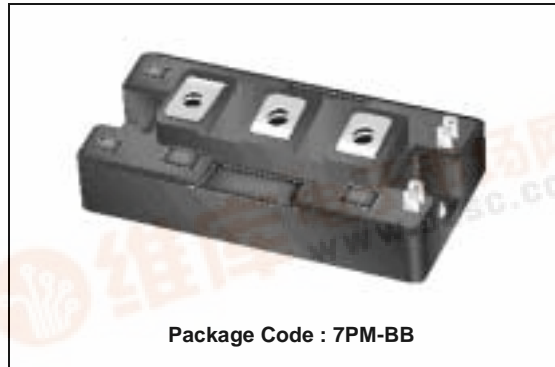
Fairchild's Insulated Gate Bipolar Transistor (IGBT) power modules provide low conduction and switching losses as well as short circuit ruggedness. They are designed for applications such as motor control, uninterrupted power supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

#### Features

- UL Certified No. E209204
- Short circuit rated 10us @  $T_C = 100^\circ\text{C}$ ,  $V_{GE} = 15\text{V}$
- High speed switching
- Low saturation voltage :  $V_{CE(sat)} = 2.2\text{V}$  @  $I_C = 200\text{A}$
- High input impedance
- Fast & soft anti-parallel FWD

#### Application

- Boost (Step Up) Converter



#### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	FMBL1G200US60	Units
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C = 25^\circ\text{C}$	200	A
$I_{CM(1)}$	Pulsed Collector Current	400	A
$I_F$	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	200	A
$I_{FM}$	Diode Maximum Forward Current	400	A
$T_{SC}$	Short Circuit Withstand Time @ $T_C = 100^\circ\text{C}$	10	us
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	830	W
$T_J$	Operating Junction Temperature	-40 to +150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-40 to +125	$^\circ\text{C}$
$V_{iso}$	Isolation Voltage @ AC 1minute	2500	V
Mounting Torque	Power Terminals Screw : M5	2.0	N.m
	Mounting Screw : M6	2.5	N.m

**Notes :**

(1) Repetitive rating : Pulse width limited by max. junction temperature



## Electrical Characteristics of IGBT T<sub>C</sub> = 25°C unless otherwise noted

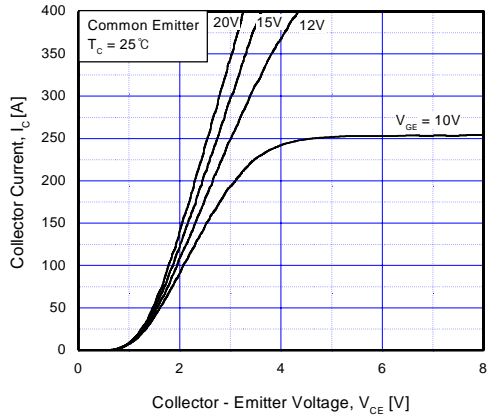
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coeff. of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	V/°C
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	$\mu A$
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 0V, I_C = 200mA$	5.0	--	8.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 200A, V_{GE} = 15V$	--	2.2	2.8	V
<b>Dynamic Characteristics</b>						
$C_{ies}$	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$	--	14600	--	pF
$C_{oes}$	Output Capacitance		--	2170	--	pF
$C_{res}$	Reverse Transfer Capacitance		--	500	--	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 200A,$ $R_G = 1.8\Omega, V_{GE} = 15V$ Inductive Load, $T_C = 25^\circ C$	--	120	--	ns
$t_r$	Rise Time		--	75	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	200	250	ns
$t_f$	Fall Time		--	90	200	ns
$E_{on}$	Turn-On Switching Loss		--	3.6	--	mJ
$E_{off}$	Turn-Off Switching Loss		--	8.7	--	mJ
$E_{ts}$	Total Switching Loss	--	12.3	--	mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 200A,$ $R_G = 1.8\Omega, V_{GE} = 15V$ Inductive Load, $T_C = 125^\circ C$	--	220	--	ns
$t_r$	Rise Time		--	100	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	290	--	ns
$t_f$	Fall Time		--	210	--	ns
$E_{on}$	Turn-On Switching Loss		--	4.8	--	mJ
$E_{off}$	Turn-Off Switching Loss		--	11.8	--	mJ
$E_{ts}$	Total Switching Loss	--	16.6	--	mJ	
$T_{sc}$	Short Circuit Withstand Time	$V_{CC} = 300V, V_{GE} = 15V$ @ $T_C = 100^\circ C$	10	--	--	us
$Q_g$	Total Gate Charge	$V_{CE} = 300V, I_C = 200A,$ $V_{GE} = 15V$	--	820	900	nC
$Q_{ge}$	Gate-Emitter Charge		--	170	--	nC
$Q_{gc}$	Gate-Collector Charge		--	365	--	nC

**Electrical Characteristics of DIODE**  $T_C = 25^\circ\text{C}$  unless otherwise noted

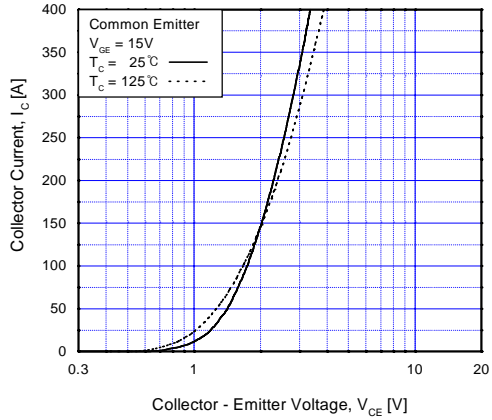
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
$V_{FM}$	Diode Forward Voltage	$I_F = 200\text{A}$	$T_C = 25^\circ\text{C}$	--	1.9	2.8	V
			$T_C = 100^\circ\text{C}$	--	1.8	--	
$t_{rr}$	Diode Reverse Recovery Time		$T_C = 25^\circ\text{C}$	--	90	130	ns
			$T_C = 100^\circ\text{C}$	--	130	--	
$I_{rr}$	Diode Peak Reverse Recovery Current	$I_F = 200\text{A}$ $di / dt = 400 \text{ A/us}$	$T_C = 25^\circ\text{C}$	--	19	25	A
			$T_C = 100^\circ\text{C}$	--	25	--	
$Q_{rr}$	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	--	855	1600	nC
			$T_C = 100^\circ\text{C}$	--	1625	--	

**Thermal Characteristics**

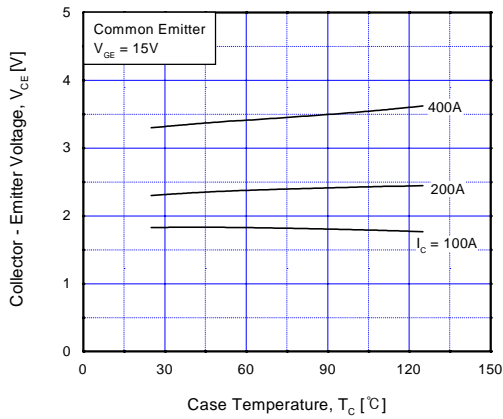
Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/2 Module)	--	0.15	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/2 Module)	--	0.35	$^\circ\text{C/W}$
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.03	--	$^\circ\text{C/W}$
Weight	Weight of Module	--	270	g



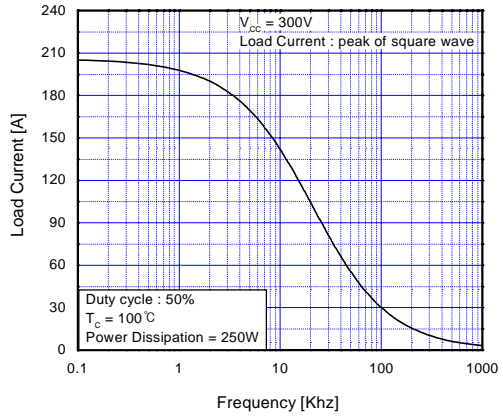
**Fig 1. Typical Output Characteristics**



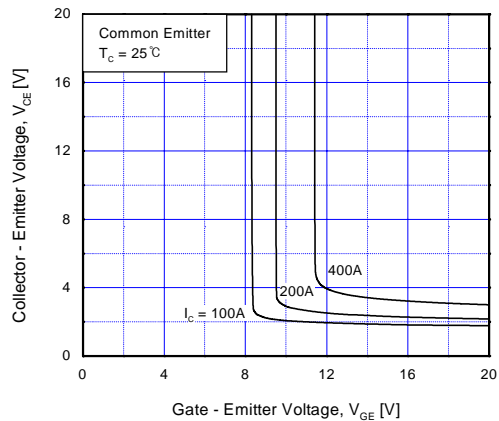
**Fig 2. Typical Saturation Voltage Characteristics**



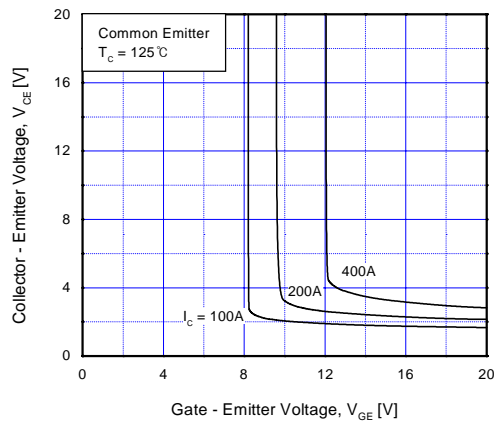
**Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level**



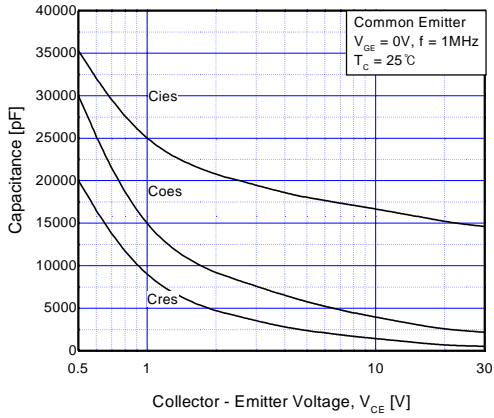
**Fig 4. Load Current vs. Frequency**



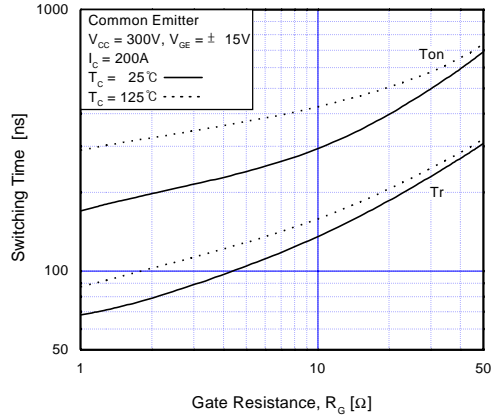
**Fig 5. Saturation Voltage vs.  $V_{GE}$**



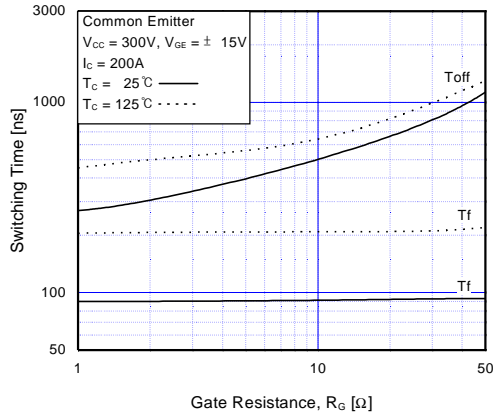
**Fig 6. Saturation Voltage vs.  $V_{GE}$**



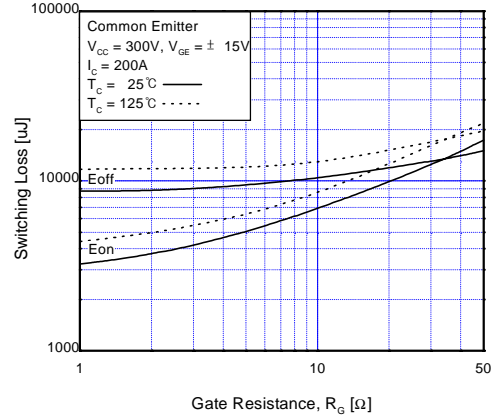
**Fig 7. Capacitance Characteristics**



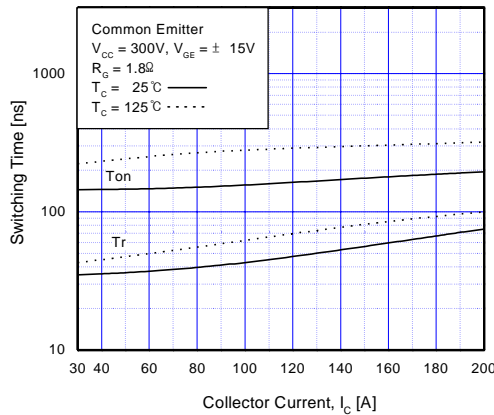
**Fig 8. Turn-On Characteristics vs. Gate Resistance**



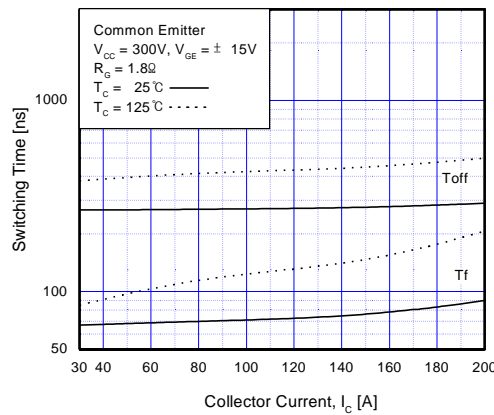
**Fig 9. Turn-Off Characteristics vs. Gate Resistance**



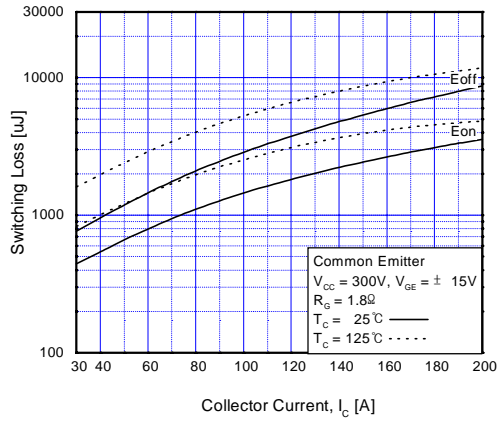
**Fig 10. Switching Loss vs. Gate Resistance**



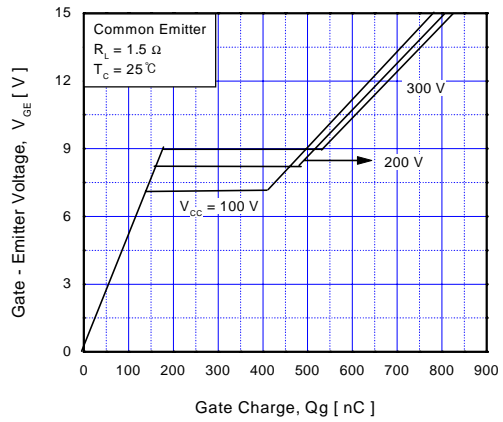
**Fig 11. Turn-On Characteristics vs. Collector Current**



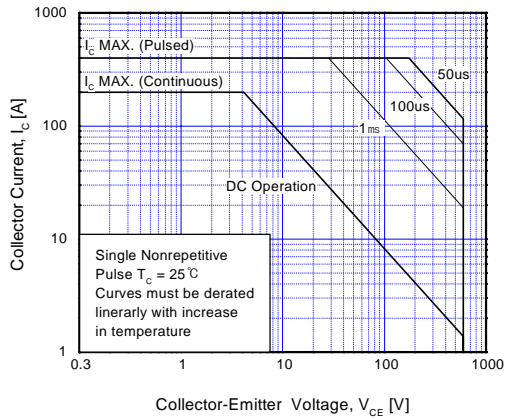
**Fig 12. Turn-Off Characteristics vs. Collector Current**



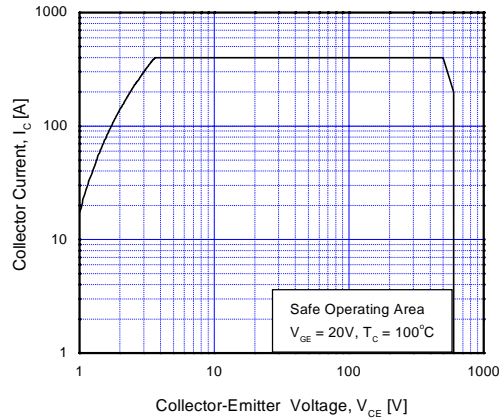
**Fig 13. Switching Loss vs. Collector Current**



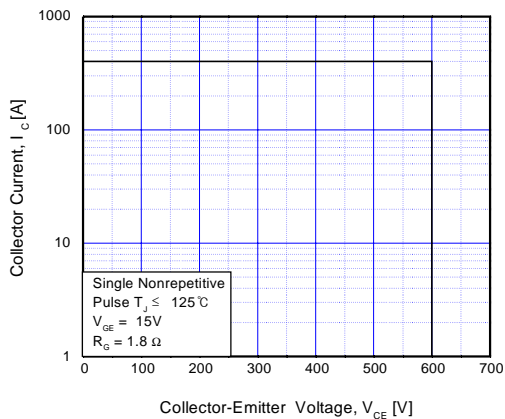
**Fig 14. Gate Charge Characteristics**



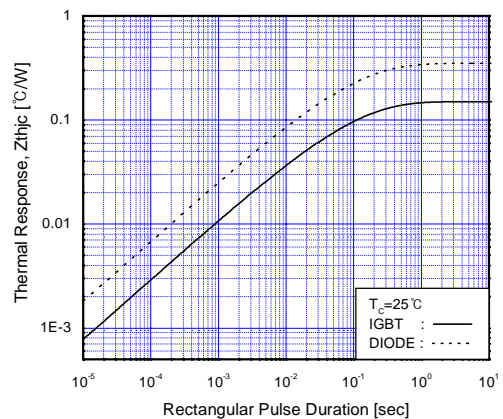
**Fig 15. SOA Characteristics**



**Fig 16. Turn-Off SOA Characteristics**



**Fig 17. RBSOA Characteristics**



**Fig 18. Transient Thermal Impedance**

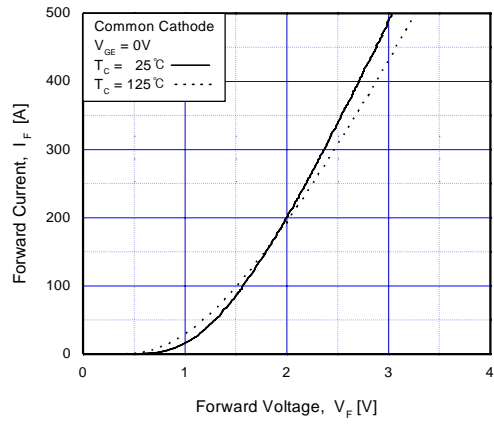


Fig 19. Forward Characteristics

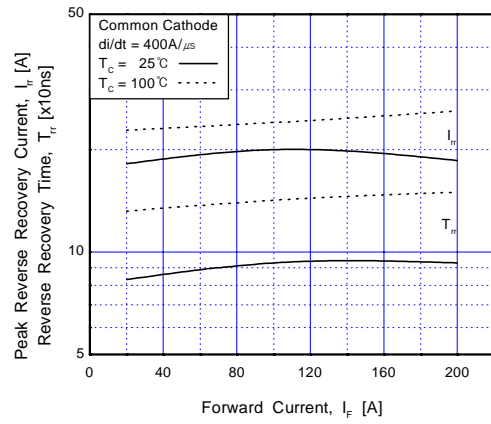
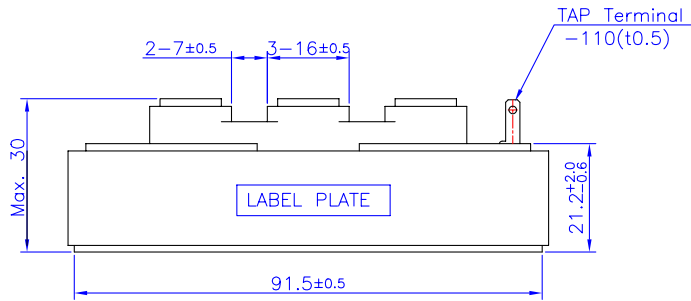
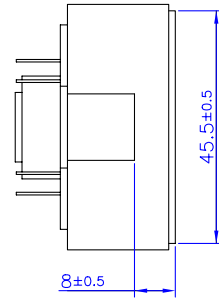
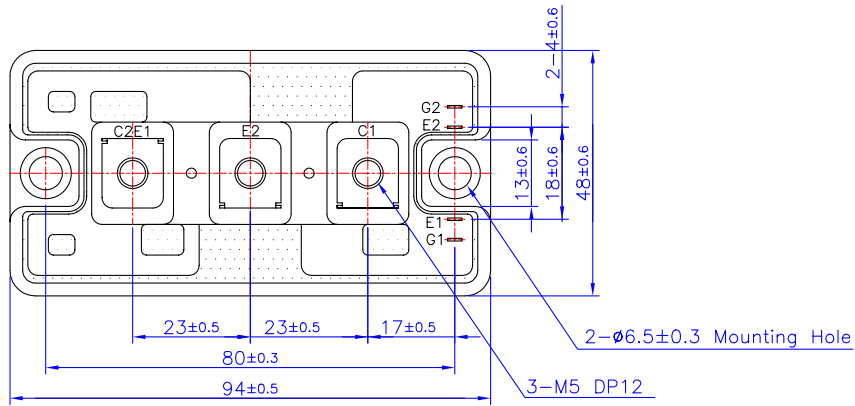


Fig 20. Reverse Recovery Characteristics

Package Dimension

7PM-BB (FS PKG CODE BE)



Dimensions in Millimeters



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